Review of: "This field becomes Especially, nanoelectronic lithography has great potential to set new standards for making miniature, low-cost, and light-weight optics that can be used in many fields of applications."

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The ability to produce large micro- and nanostructures on non-planar surfaces is important for many applications such as optics, optoelectronics, nanophotonics, imaging technology, NEMS, and microfluidics. With this, it is very difficult to create large nanostructures on curved or non-planar surfaces using existing patterning methods. Furthermore, a variety of current nanopatterning technologies, such as electron beam lithography, optical lithography, interference lithography (IL), etc., cannot meet all the practical demands of industrial applications in terms of high resolution, high power, low cost, large area, and patterns on non-flat and curved surfaces. Therefore, a new high-volume nano-manufacturing technology urgently needs to be exploited and developed to meet the extraordinary needs of growing markets. Lithography in nanoelectronics is currently considered as a promising low-cost, high-throughput, and high-resolution nanopatterning method, especially for the production of large-scale small/nanopatterns and complex 3D structures, as well as the aspect. The above characteristics of the ratio regarding these outstanding advantages have also resulted. This field becomes Especially, nanoelectronic lithography has great potential to set new standards for making miniature, low-cost, and light-weight optics that can be used in many fields of applications.

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